

ABSTRACT

A method of leading an electron beam (22) radiated from an electron emitter (14) through openings provided in a stencil mask (18) to a sensitive sample (12) and exposing it includes placing the electron beam under a low field intensity where the electron beam progresses at a slow speed until reaching the openings of the stencil mask and thereafter placing the electron beam having passed through the openings of the stencil mask under a high field intensity where the electron beam progresses at a high speed. An apparatus for electron beam projection lithography comprises an electron emitter, a stencil mask having openings for permitting the electron beam radiated from the electron emitter to pass through, a base (16) for supporting an exposure sample, and a device for placing the electron beam under a low field intensity as well as a high field generator for placing the electron beam under a high field intensity.



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